

NOC: Fundamentals of electronic materials and devices

Exam information sheet

Useful constants

$$1 \text{ eV} = 1.6 \times 10^{-19} \text{ J}$$

$$h = 6.626 \times 10^{-34} \text{ Js}$$

$$c = 3 \times 10^8 \text{ ms}^{-1}$$

$$k_B = 1.38 \times 10^{-23} \text{ JK}^{-1}$$

$$e = 1.6 \times 10^{-19} \text{ C}$$

$$\epsilon_0 = 8.854 \times 10^{-12} \text{ Fm}^{-1}$$

$$k_B = 1.38 \times 10^{-23} \text{ JK}^{-1}$$

$$N_A = 6.023 \times 10^{23}$$

Useful relations

$$f(E) = \frac{1}{1 + \exp\left[\frac{E-E_F}{k_B T}\right]} \quad g(E) = 8\pi\sqrt{2}\left(\frac{m_e}{h^2}\right)^{3/2}\sqrt{E} \quad n(E) = f(E)g(E)$$

$$n_i = \sqrt{N_c N_v} \exp\left(-\frac{E_g}{2k_B T}\right) \quad np = n_i^2$$

$$N_c = 2\left(\frac{2\pi m_e^* k_B T}{h^2}\right)^{3/2} \quad N_v = 2\left(\frac{2\pi m_h^* k_B T}{h^2}\right)^{3/2}$$

$$E_{Fi} = \frac{E_g}{2} - \frac{1}{2}k_B T \ln\left(\frac{N_c}{N_v}\right)$$

$$E_{Fn} - E_{Fi} = k_B T \ln\left(\frac{n}{n_i}\right) \quad E_{Fp} - E_{Fi} = -k_B T \ln\left(\frac{p}{n_i}\right)$$

$$\sigma = ne\mu_e + pe\mu_h$$

Schottky junction : $J = J_0 \exp\left(\frac{eV}{k_B T}\right)$ where $J_0 = AT^2 \exp\left(-\frac{\phi_B}{k_B T}\right)$

pn junction contact potential : $V_0 = \frac{k_B T}{e} \ln\left(\frac{n_n p_p}{n_i^2}\right)$

pn junction depletion width : $w_0 = \sqrt{\frac{2\epsilon_0\epsilon_r(N_A + N_D)V_0}{eN_A N_D}}$; $w_n N_D = w_p N_A$

pn junction forward bias : $J = J_0 \exp\left(\frac{eV}{k_B T}\right)$ where $J_0 = n_i^2 e \left[\frac{D_h}{L_h N_D} + \frac{D_e}{L_e N_A} \right]$

$$D_e = \frac{k_B T \mu_e}{e}; D_h = \frac{k_B T \mu_h}{e}; L_e = \sqrt{D_e \tau_e}; L_h = \sqrt{D_h \tau_h}$$

MOS junction : $\phi_s = \frac{e^2 N_A w_D^2}{2\epsilon_0 \epsilon_r}$ channel width : $x_m = w_D \left(\frac{\sqrt{2} - 1}{\sqrt{2}} \right)$

Energy and wavelength : $E = \frac{hc}{\lambda}$ Beer-Lambert's law : $I = I_0 \exp(-\alpha x)$

Excess carrier concentration under illumination: $\frac{d\Delta p}{dt} = G_{ph} - \frac{\Delta p}{\tau_h}$

Solar cell open circuit voltage : $V_{oc} = \frac{k_B T}{e} \ln\left(\frac{J_{ph}}{J_0}\right)$

where J_0 is defined above for a pn junction and J_{sc} is the short circuit current